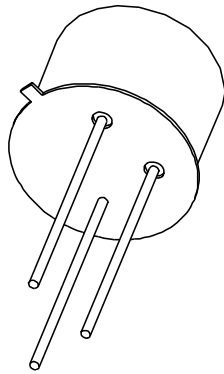


# DATA SHEET



## **BSS61; BSS62** PNP Darlington transistors

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 May 14

# PNP Darlington transistors

# BSS61; BSS62

### FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

### APPLICATIONS

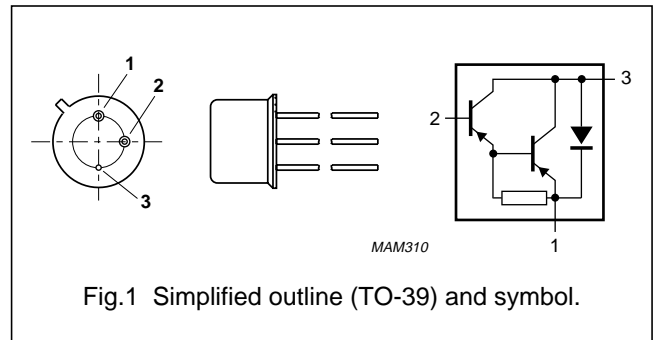
- Industrial high gain amplification.

### DESCRIPTION

PNP Darlington transistor in a TO-39 metal package.  
 NPN complements: BSS51 and BSS52.

### PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter				
	BSS61		–	–	–80	V
	BSS62		–	–	–90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0				
	BSS61		–	–	–60	V
	BSS62		–	–	–80	V
I <sub>C</sub>	collector current (DC)		–	–	–1	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	–	0.8	W
		T <sub>case</sub> ≤ 25 °C	–	–	5	W
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = –500 mA; V <sub>CE</sub> = –10 V	2000	–	–	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = –500 mA; V <sub>CE</sub> = –5 V; f = 100 MHz	–	200	–	MHz

## PNP Darlington transistors

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSS61		–	–80	V
	BSS62		–	–90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0			
	BSS61		–	–60	V
	BSS62		–	–80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–1	A
I <sub>CM</sub>	peak collector current		–	–2	A
I <sub>B</sub>	base current (DC)		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	0.8	W
		T <sub>case</sub> ≤ 25 °C	–	5	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	200	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air	220	K/W
R <sub>th j-c</sub>	thermal resistance from junction to case		35	K/W

## PNP Darlington transistors

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**CHARACTERISTICS**T<sub>j</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CES</sub>	collector cut-off current BSS61 BSS62	V <sub>BE</sub> = 0; V <sub>CE</sub> = -60 V	-	-	-50	nA
		V <sub>BE</sub> = 0; V <sub>CE</sub> = -80 V	-	-	-50	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = -4 V	-	-	-100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = -150 mA; V <sub>CE</sub> = -10 V	1000	-	-	
		I <sub>C</sub> = -500 mA; V <sub>CE</sub> = -10 V	2000	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -0.5 mA	-	-	-1.3	V
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -0.5 mA; T <sub>j</sub> = 200 °C	-	-	-1.3	V
V <sub>CEsat</sub>	collector-emitter saturation voltage BSS61	I <sub>C</sub> = -1 A; I <sub>B</sub> = -1 mA	-	-	-1.6	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -1 mA; T <sub>j</sub> = 200 °C	-	-	-1.6	V
V <sub>CEsat</sub>	collector-emitter saturation voltage BSS62	I <sub>C</sub> = -1 A; I <sub>B</sub> = -4 mA	-	-	-1.6	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -4 mA; T <sub>j</sub> = 200 °C	-	-	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -0.5 mA	-	-	-1.9	V
V <sub>BEsat</sub>	base-emitter saturation voltage BSS61 BSS62	I <sub>C</sub> = -1 A; I <sub>B</sub> = -1 mA	-	-	-2.2	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -4 mA	-	-	-2.2	V
f <sub>T</sub>	transition frequency	I <sub>C</sub> = -500 mA; V <sub>CE</sub> = -5 V; f = 100 MHz	-	200	-	MHz
<b>Switching times (between 10% and 90% levels)</b>						
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = -500 mA; I <sub>Bon</sub> = -0.5 mA; I <sub>Boff</sub> = 0.5 mA	-	0.5	-	μs
		I <sub>Con</sub> = -1 A; I <sub>Bon</sub> = -1 mA; I <sub>Boff</sub> = 1 mA	-	0.4	-	μs
t <sub>off</sub>	turn-off time	I <sub>Con</sub> = -500 mA; I <sub>Bon</sub> = -0.5 mA; I <sub>Boff</sub> = 0.5 mA	-	0.7	-	μs
		I <sub>Con</sub> = -1 A; I <sub>Bon</sub> = -1 mA; I <sub>Boff</sub> = 1 mA	-	1.5	-	μs

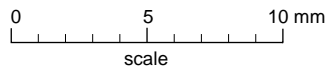
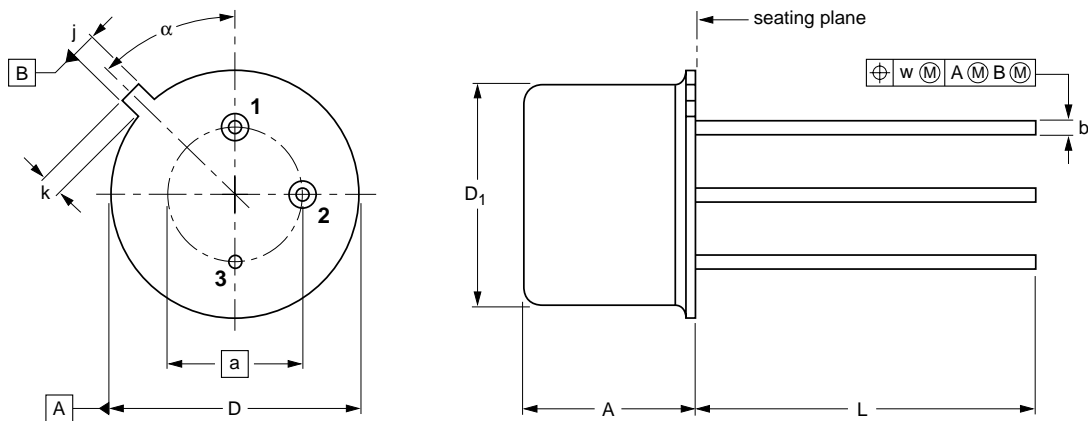
PNP Darlington transistors

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PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D <sub>1</sub>	j	k	L	w	$\alpha$
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

## PNP Darlington transistors

## BSS61; BSS62

**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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PNP Darlington transistors

BSS61; BSS62

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